[illegible] (@ T_C = 25°C unless otherwise specified)

[illegible]	[illegible]	[illegible]	[illegible]			[illegible]
			[illegible]	[illegible]	[illegible]	
Peak forward voltage	I_T=360A, t_P=380	V_T			1.80	V
Repetitive peak off-state current	V_D = V_{DRM},T_{vj} = 25	I_{DRM}			100	A
	V_D = V_{DRM},T_{vj} = 125				40	mA
Reverse leakage current	V_R = V_{RRM},T_{vj} = 25	I_{RRM}			100	A
	V_R = V_{RRM},T_{vj} = 125				40	mA
Threshold voltage	For power loss calculation only T_{vj} = 125 ,	V_{TO}			0.9	V
Dynamic resistance	T_{vj} = 125 ,	r_T			2	
Triggering gate current	V_D=12V R_L	ITO				

[illegible]

[illegible]

Unit of measurement: mm

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